

isc Silicon PNP Darlington Power Transistor

BDT64F/AF/BF/CF

DESCRIPTION

- Collector Current $-I_C = -12A$
- High DC Current Gain $-h_{FE} = 1000(\text{Min}) @ I_C = -5A$
- Complement to Type BDT65F/AF/BF/CF

APPLICATIONS

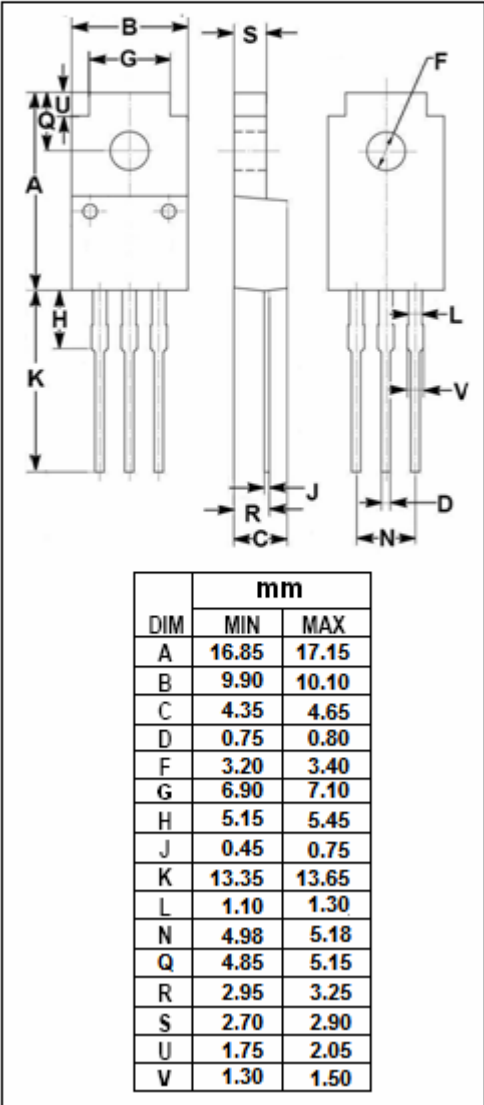
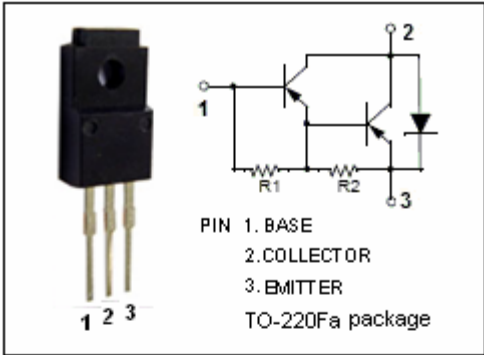
- Designed for audio output stages and general purpose amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a = 25^{\circ}C$)

SYMBOL	PARAMETER		VALUE	UNIT
V_{CER}	Collector-Emitter Voltage	BDT64F	-60	V
		BDT64AF	-80	
		BDT64BF	-100	
		BDT64CF	-120	
V_{CEO}	Collector-Emitter Voltage	BDT64F	-60	V
		BDT64AF	-80	
		BDT64BF	-100	
		BDT64CF	-120	
V_{EBO}	Emitter-Base Voltage		-5	V
I_C	Collector Current-Continuous		-12	A
I_{CM}	Collector Current-Peak		-20	A
I_B	Base Current-Continuous		-0.5	A
P_C	Collector Power Dissipation @ $T_C = 25^{\circ}C$		39	W
T_J	Junction Temperature		150	$^{\circ}C$
T_{stg}	Storage Temperature Range		-65~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	5.7	$^{\circ}C/W$



isc Silicon PNP Darlington Power Transistor

BDT64F/AF/BF/CF

ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	BDT64F	$I_C = -30\text{mA}; I_B = 0$	-60			V
		BDT64AF		-80			
		BDT64BF		-100			
		BDT64CF		-120			
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage		$I_C = -5\text{A}; I_B = -20\text{mA}$			-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage		$I_C = -10\text{A}; I_B = -100\text{mA}$			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage		$I_C = -5\text{A}; V_{CE} = -4\text{V}$			-2.5	V
V_{ECF}	C-E Diode Forward Voltage		$I_F = -5\text{A}$			-2.0	V
I_{CEO}	Collector Cutoff Current		$V_{CE} = \frac{1}{2}V_{CEOmax}; I_B = 0$			-1	mA
I_{CBO}	Collector Cutoff Current		$V_{CB} = V_{CB0max}; I_E = 0$ $V_{CB} = \frac{1}{2}V_{CB0max}; I_E = 0; T_C = 150^{\circ}\text{C}$			-0.4 -2	mA
I_{EBO}	Emitter Cutoff Current		$V_{EB} = -5\text{V}; I_C = 0$			-5	mA
h_{FE-1}	DC Current Gain		$I_C = -1\text{A}; V_{CE} = -4\text{V}$		4000		
h_{FE-2}	DC Current Gain		$I_C = -5\text{A}; V_{CE} = -4\text{V}$	1000			
h_{FE-3}	DC Current Gain		$I_C = -12\text{A}; V_{CE} = -4\text{V}$		800		
C_{OB}	Output Capacitance		$I_E = 0; V_{CB} = -10\text{V}; f_{test} = 1\text{MHz}$		200		pF

Switching times

t_{on}	Turn-On Time	$I_C = -5\text{A}; I_{B1} = -I_{B2} = -20\text{mA};$ $V_{CC} = -30\text{V}$		0.5	2	μs
t_{off}	Turn-Off Time			2.5	5	μs